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HSML, P.C.

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Sheet 1 of 1

<b>FORM 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b>  <b>IN AN APPLICATION</b>  (Use several sheets if necessary)	Docket Number:	Application Number:
	10873.1761USWO	10549494
	Applicant: SASAKI	
	Filing Date: September 15, 2005	Group Art Unit: Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	5,868,837	February 1999	DiSalvo, et al.				
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	60-122797	July, 1985	Japan			Abstract & Partial	
	2001-53013	February, 2001	Japan			Abstract	
	2002-68896	March, 2002	Japan			Abstract & Partial	
	1 201 793	May, 2002	EPO				
	2002-293696	October, 2002	October 2002			Abstract & Partial	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
		Grzegory, et al., "III-V Nitrides - Thermodynamics and Crystal Growth at High N <sub>2</sub> Pressure". J. Phys. Chem. Solids, vol. 56, no. 34, pp. 639-647, 1995					
		Song, et al., "Buld GaN single crystals: growth conditions by flux method". Journal of Crystal Growth 247 (2003), pp. 275-278					
		Kawamura, et al., "Synthesis of Bulk GaN Single Crystals Using Na-Ca Flux". Jpn. J. Appl. Phys. vol. 41, (2002), pp. L1440-L1442					

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PATENT TRADEMARK OFFICE

EXAMINER	/Matthew Song/	DATE CONSIDERED	08/30/2008
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.			

\*Substitute Disclosure Statement Form (PTO-1449)

Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

PAGE 4/54 \* RCVD AT 12/13/2005 3:14:27 PM [Eastern Standard Time] \* SVR:USPTO-EFXRF-6/27 \* DNIS:2738300 \* CSID:612-455-3801 \* DURATION (mm-ss):19-08

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /MS/